SEMICONDUCTOR SENSOR AND FABRICATION THEREOF

Publication number:

JP2000243783

Publication date:

2000-09-08

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Applicant:

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Classification:

- International:

H01L21/60; H01L21/02; (IPC1-7): H01L21/60

- European:

Application number:

JP19990042748 19990222

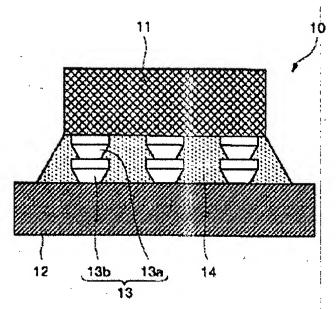
Priority number(s):

JP19990042748 19990222

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Abstract of JP2000243783

PROBLEM TO BE SOLVED: To provide a semiconductor sensor comprising a semiconductor sensor, in which stress and flexure hindering miniaturization of semiconductor sensor can be reduced. SOLUTION: When a semiconductor sensor chip 11 is a bare chip mounted on a substrate 12, a metal pole 13 for conducting an electrode on the rear surface of the sensor chip with a wiring pattern on the substrate is provided. The metal pole is formed by stacking a first metal protrusion 13a on a second metal protrusion 13b. A plurality of metal poles are arranged adjacently, and the gap between the metal poles is filled with a bonding material. Since a significantly high metal pole can be formed as compared with a conventional one, transmission of stress and flexure is suppressed, and the semiconductor sensor can sustain high measurement accuracy. Consequently, the semiconductor sensor can be miniaturized.



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